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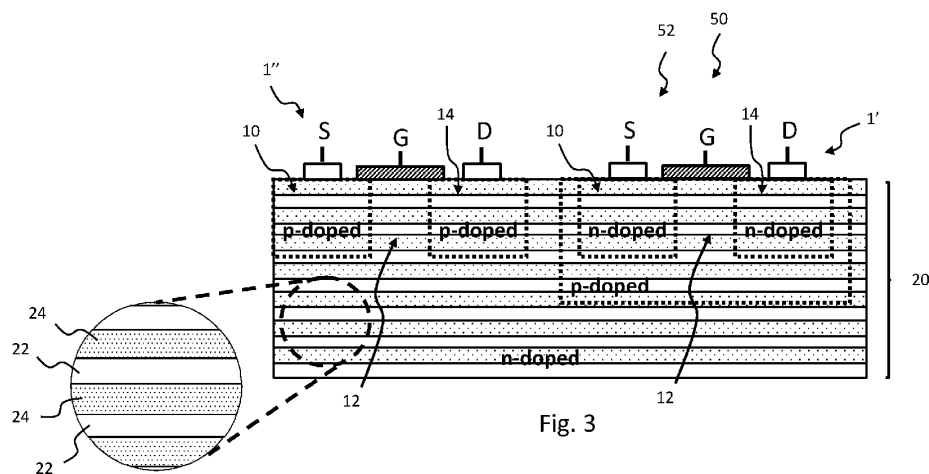


Fig. 3

(57) Abstract: A transistor (1) comprising a source (10), a body (12) and a drain (14), the transistor (1) further comprising a plurality of semiconductor layers (20), wherein layers of the plurality of semiconductor layers (20) are made of AlGaIn or GaN, and wherein the plurality of semiconductor layers (20) is configured such that an aluminum content changes between each consecutive layer such that every second layer has a lower aluminum content than the neighboring mutually opposite layers thereof, wherein the transistor (1) is either a N-channel metal-oxide-semiconductor, NMOS, transistor (1'), wherein part of the plurality of semiconductor layers (20) is p-doped and forms part of the body (12) of the NMOS transistor (1'); or a P-channel metal-oxide-semiconductor, PMOS, transistor (1''), wherein part of the plurality of semiconductor layers (20) is p-doped and forms part of the source (10) or the drain (14) of the PMOS transistor (1'').

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